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DS14C88/DS14C88T QUAD CMOS Line Driver

General Description

The DS14C88 and DS14C88T, pin-for-pin compatible to the DS1488/MC1488, are line drivers designed to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices translate standard TTL/CMOS logic levels to levels conforming to EIA-232-D and CCITT V.28 standards.

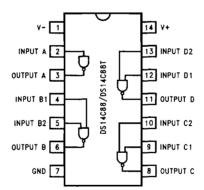
The device is fabricated in low threshold CMOS metal gate technology. The device provides very low power consumption compared to its bipolar equivalents: $500 \mu A$ (DS14C88) versus 25 mA (DS1488).

The DS14C88/DS14C88T simplifies designs by eliminating the need for external slew rate control capacitors. Slew rate control in accordance with EIA-232D is provided on-chip, eliminating the output capacitors.

Features

- Meets EIA-232D and CCITT V.28 standards
- Industrial temperature range
- -40°C to +85°C-DS14C88T
- LOW power consumption
- Wide power supply range ±5V to ±12V
- Available in SOIC package

Connection Diagram



TL/F/11105-1

Order Number DS14C88N, DS14C88M, DS14C88TJ, DS14C88TM or DS14C88TM See NS Package Number J14A, N14A or M14A

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage

V+ Pin + 13V V- Pin - 13V

Driver Input Voltage (V+) + 0.3V to GND - 0.3V

Continuous Power Dissipation @ +25°C (Note 2)

 N Package
 1513 mW

 J Package
 1935 mW

 M Package
 1063 mW

Junction Temperature + 150°C

Lead Temperature

(Soldering 4 seconds) + 260°C

Storage Temperature Range -65°C to +150°C
This Product does not meet 2000V ESD rating. (Note 9)

Recommended Operating Conditions

	Min	Max	Units
V^+ Supply (GND = 0V)	+4.5	+12.6	V
V - Supply (GND = 0V)	-4.5	-12.6	V
Operating Free Air Temp. (TA)			
DS14C88	0	+ 75	°C
DS14C88T	-40	+85	۰C

Electrical Characteristics Over Recommended Operating Conditions, unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Units	
l _{IL}	Maximum Low Input Current	V _{IN} = GND				+10	μΑ	
<u>ч</u> н	Maximum High Input Current	V _{IN} = V+		-10			μΑ	
V _{IL}	Low Level Input Voltage	V ⁺ ≥ +7V, V ⁻ ≤ -7V		GND		0.8	٧	
		V ⁺ < +7V, V ⁻ > -7V		GND		0.6	٧	
V _{IH}	High Level Input Voltage				2.0		٧+	٧
VOL	Low Level Output Level	$V_{IN} = V_{IH}$ $R_L = 3 k\Omega$ or $7 k\Omega$	$V^{+} = 4.5V, V^{-} = -4.5V$			-4.0	-3.0	V
			$V^{+} = 9V, V^{-} = 9V$			-8.0	-6.5	٧
			$V^{+} = 12V, V^{-} = -12V$			-10.5	-9.0	V
V _{OH}	High Level Output Level	$V_{IN} = V_{IL}$ $R_L = 3 k\Omega$ or $7 k\Omega$	$V^{+} = 4.5V, V^{-} = -4.5V$		3.0	4.0		V
			$V^{+} = 9V, V^{-} = -9V$		6.5	8.0		V
		01 7 132	$V^{+} = 12V, V^{-} = -$	12V	9.0	10.5		V
los+	High Level Output Short Circuit Current (Note 3)	$V_{IN} = 0.8V, V_{C}$	$V_{IN} = 0.8V, V_O = GND$ $V^+ = +12V, V^- = -12V$		-45			mA
los-	Low Level Output Short Circuit Current (Note 3)	$V_{IN} = 2.0V, V_{C}$	V _O = GND				+ 45	mA
R _{OUT}	Output Resistance	$V^{+} = V^{-} = 0$ $-2V \le V_{0} \le 1$	= GND = 0V ≤ + 2V (Note 4) (Figure 1)		300			Ω
I _{CC+}	Positive Supply Current	V _{IN} = V _{ILmax} R _L = OPEN	$V^{+} = 4.5V, V^{-} = -4.5V$				10	μ.Α
			$V^{+} = 9V, V^{-} = -9V$				30	μΑ
			$V^{+} = 12V, V^{-} = -12V$				60	μΑ
		$V_{IN} = V_{IHmin}$	$V^{+} = 4.5V, V^{-} = -$	$V^{+} = 4.5V, V^{-} = -4.5V$			50	μΑ
		R _L = OPEN	V+ = 9V, V- = -9V	DS14C88			300	μΑ
				DS14C88T			400	μА
			V ⁺ = 12V, V ⁻ = -12V	DS14C88			500	μΑ
*				DS14C88T			700	μA
I _{CC} - N	Negative Supply Current	$V_{IN} = V_{ILmax}$ $R_L = OPEN$	$V^{+} = 4.5V$	DS14C88			-10	μА
			V- = -4.5V	DS14C88T			~15	μA
			V+ = 9V,	DS14C88			-10	μА
			V- = -9V	DS14C88T			- 15	μА
			$V^{+} = 12V$,	DS14C88			-10	0 μA 0 μA 5 μA 0 μA 5 μA 5 μA
			V- = -12V	DS14C88T			~15	μA
		V _{IN} = V _{IHmin} R _L = OPEN	$V^{+} = 4.5V,$	DS14C88			-30	μА
			$V^- = -4.5V$	DS14C88T			-45	μA
			V+ = 9V,	DS14C88			-30	μΑ
			V- = -9V	DS14C88T			-45	μΑ
			V+ = 12V,	DS14C88			-60	μA
			$V^{-} = -12V$	DS14C88T			-80	μА

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Switching CharacteristicsOver Recommended Operating Conditions, unless otherwise specified (*Figures 2* and *3*) (Notes 5 and 6)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PLH}	Propagation Delay Low to High	$V^{+} = +4.5V, V^{-} = -4.5V$		1.5	6.0	μs
		$V^{+} = +9.0V, V^{-} = -9.0V$		1.2	5.0	μs
		$V^{+} = +12V, V^{-} = -12V$		1.2	4.0	μs
t _{PHL} Propagation Delay High to Low	Propagation Delay	$V^{+} = +4.5V, V^{-} = -4.5V$		1.5	6.0	μs
	High to Low	$V^{+} = +9.0V, V^{-} = -9.0V$		1.35	5.0	μs
		$V^{+} = +12V, V^{-} = -12V$		1.3	4.0	μs
t _r	Rise Time (Note 7)		0.2	1.0		μs
t _f	Fall Time (Note 7)		0.2	1.0		μs
	Typical Propagation Delay Skew	$V^{+} = +4.5V, V^{-} = -4.5V$		250		ns
		$V^{+} = +9.0V, V^{-} = -9.0V$		200		ns
		$V^+ = +12V, V^- = -12V$		150		ns
S _R	Output Slew Rate (Note 7)	$R_L = 3 k\Omega \text{ to } 7 k\Omega$ $C_L = 15 \text{ pF to } 2500 \text{ pF}$			30	V/µs

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.

Note 2: Derate N Package 12.1 mW/°C, J Package 12.9 mW/°C, and M Package 8.5 mW/°C above +25°C.

Note 3: IOS+ and IOS- values are for one output at a time. If more than one output is shorted simultaneously, the device dissipation may be exceeded.

Note 4: Power supply (V+, V-) and GND pins are connected to ground for the Output Resistance Test (R_O).

Note 5: AC input test waveforms for test purposes: $t_{f} = t_{f} \le 20$ ns, $V_{IH} = 2V$, $V_{IL} = 0.8V$ (0.6V at $V^{+} = 4.5V$, $V^{-} = -4.5V$)

Note 8: Input rise and rall times must not exceed 5 μ s.

Note 7: The output slew rate, rise time, and fall time are measured from the +3.0V to the -3.0V level on the output waveform.

Note 8: CL include jig and probe capacitances.

Note 9: ESD Rating (HBM, 1.5 k Ω , 100 pF) \geq 1.0 kV.

Parameter Measure Information

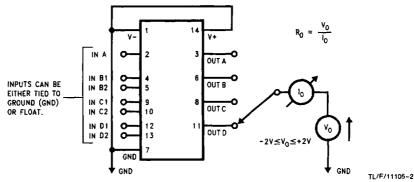


FIGURE 1. Output Resistance Test Circuit (Power-Off)

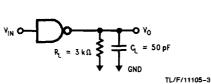


FIGURE 2. Driver Load Circuit (Note 8)

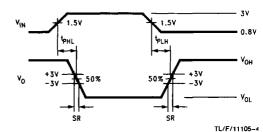


FIGURE 3. Driver Switching Waveform

Typical Application Information

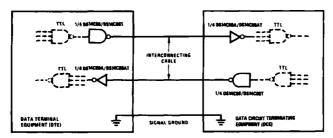


FIGURE 4. EIA-232D Data Transmission

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